

2MBI600VN-120-50

IGBT Modules

IGBT MODULE (V series) 1200V / 600A / 2 in one package

Features

- High speed switching
- Voltage drive
- Low Inductance module structure

Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial machines, such as Welding machines



Maximum Ratings and Characteristics

Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items	Symbols	Conditions	Maximum ratings	Units
Inverter	Collector-Emitter voltage	V_{CES}	1200	V
	Gate-Emitter voltage	V_{GES}	± 20	V
	Collector current	Continuous	Tc=25°C	750
			Tc=100°C	600
		Ic pulse	1ms	1200
		-Ic		600
		-Ic pulse	1ms	1200
	Collector power dissipation	Pc	1 device	3750
Junction temperature			Tj	175
Operating junction temperature (under switching conditions)			Tjop	150
Case temperature			Tc	125
Storage temperature			Tstg	-40 to +125
Isolation voltage	between terminal and copper base (*1)	AC : 1min.	2500	VAC
	between thermistor and others (*2)			
Screw torque	Mounting (*3)		3.5	N m
	Terminals (*4)		4.5	

Note *1: All terminals should be connected together during the test.

Note *2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note *3: Recommendable value : Mounting : 2.5-3.5 Nm (M5) Note *4: Recommendable value : Terminals : 3.5-4.5 Nm (M6)

Electrical characteristics (at Tj= 25°C unless otherwise specified)

Items		Symbols	Conditions		Characteristics			Units
					min.	typ.	max.	
Inverter	Zero gate voltage collector current	I _{CES}	V _{GE} = 0V, V _{CE} = 1200V		-	-	3.0	mA
	Gate-Emitter leakage current	I _{GES}	V _{CE} = 0V, V _{GE} = ±20V		-	-	600	nA
	Gate-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _C = 600mA		6.0	6.5	7.0	V
	Collector-Emitter saturation voltage	V _{CE (sat)} (terminal)	V _{GE} = 15V I _C = 600A	T _J =25°C	-	2.65	3.10	V
				T _J =125°C	-	3.00	-	
				T _J =150°C	-	3.05	-	
		V _{CE (sat)} (chip)		T _J =25°C	-	1.85	2.30	
				T _J =125°C	-	2.20	-	
	Internal gate resistance	R _{g(int)}	-		-	1.25	-	Ω
	Input capacitance	C _{ies}	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz		-	48	-	nF
	Turn-on time	t _{on}	V _{CC} = 600V		-	550	-	nsec
		t _r	I _C = 600A		-	180	-	
		t _{r (i)}	V _{GE} = ±15V		-	120	-	
	Turn-off time	t _{off}	R _G = 0.62Ω		-	1050	-	nsec
		t _f	L _S = 80nH		-	110	-	
Forward on voltage	V _F (terminal)	V _{GE} = 0V I _F = 600A	T _J =25°C	-	2.50	3.00	V	
			T _J =125°C	-	2.65	-		
			T _J =150°C	-	2.60	-		
	V _F (chip)		T _J =25°C	-	1.70	2.15		
			T _J =125°C	-	1.85	-		
Reverse recovery time	t _{rr}	I _F = 600A		-	200	-	nsec	
Thermistor	Resistance	R	T=25°C	-	5000	-	Ω	
			T=100°C	465	495	520		
	B value	B	T=25/50°C		3305	3375	3450	K

● Thermal resistance characteristics

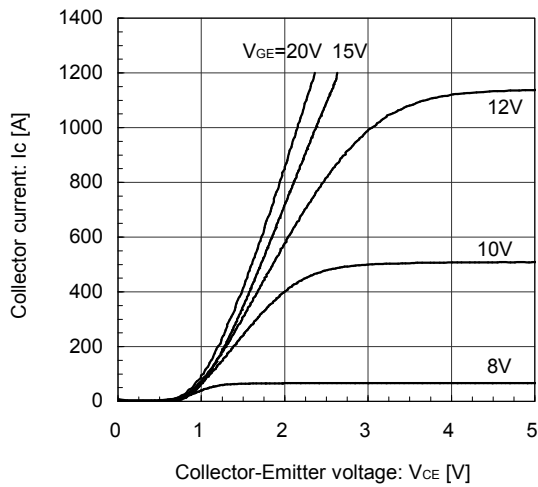
Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	Rth(j-c)	Inverter IGBT	-	-	0.04	°C/W
		Inverter FWD	-	-	0.06	
Contact thermal resistance (1device) (*5)	Rth(c-f)	with Thermal Compound	-	0.0167	-	

Note *5: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

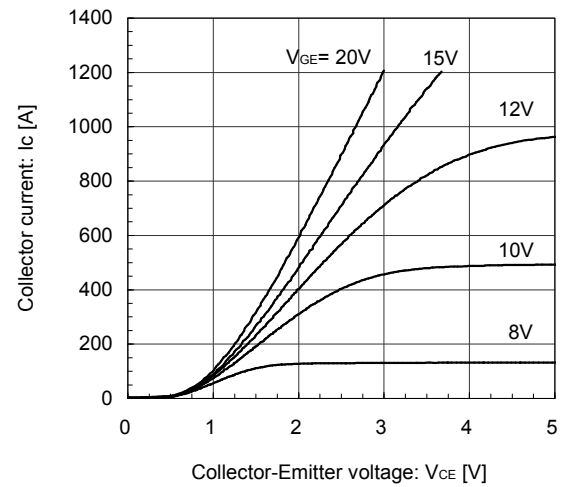
[INVERTER]

Collector current vs. Collector-Emittter voltage (typ.)
 $T_j = 25^\circ\text{C}$ / chip



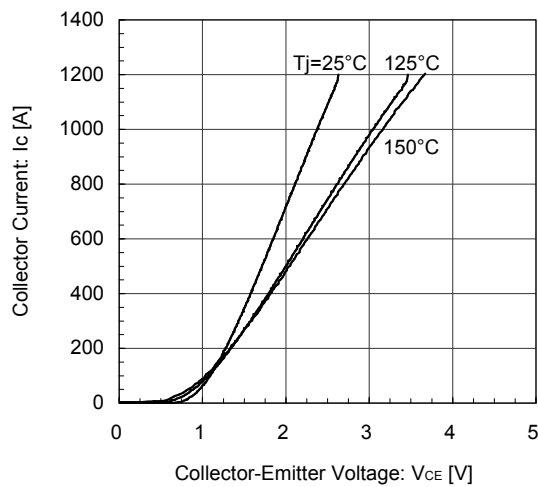
[INVERTER]

Collector current vs. Collector-Emittter voltage (typ.)
 $T_j = 150^\circ\text{C}$ / chip



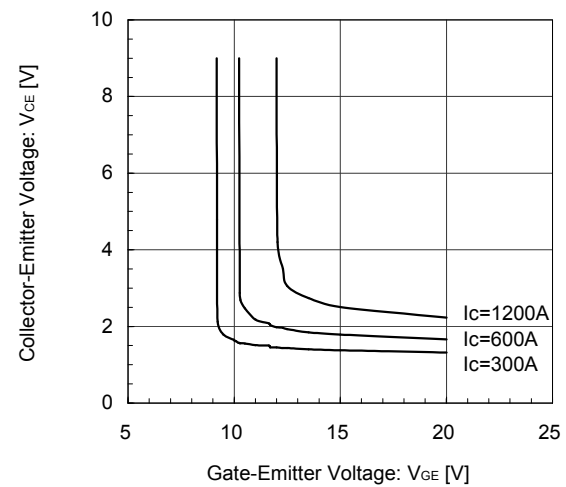
[INVERTER]

Collector current vs. Collector-Emittter voltage (typ.)
 $V_{GE} = 15\text{V}$ / chip



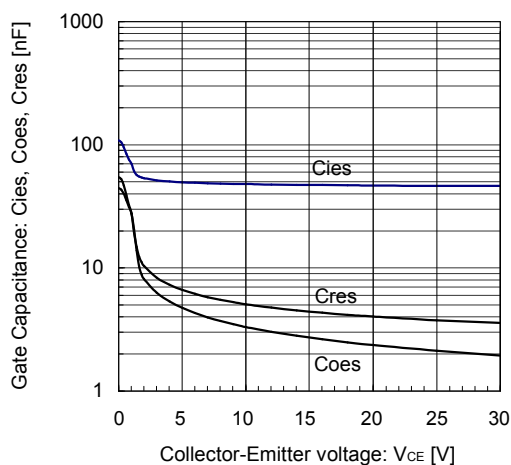
[INVERTER]

Collector-Emittter voltage vs. Gate-Emittter voltage (typ.)
 $T_j = 25^\circ\text{C}$ / chip



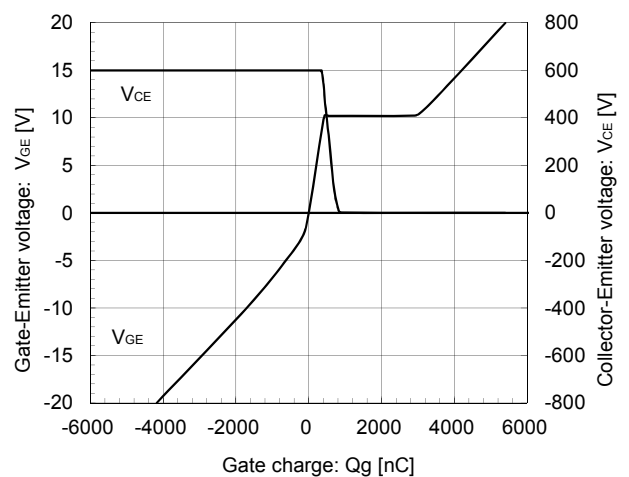
[INVERTER]

Gate Capacitance vs. Collector-Emittter Voltage (typ.)
 $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$, $T_j = 25^\circ\text{C}$



[INVERTER]

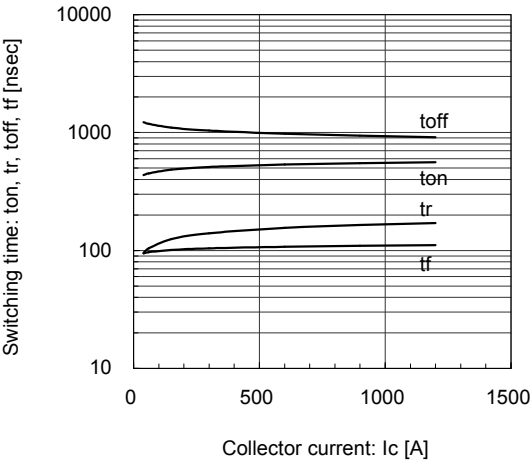
Dynamic Gate Charge (typ.)
 $V_{CC} = 600\text{V}$, $I_C = 600\text{A}$, $T_j = 25^\circ\text{C}$



[INVERTER]

Switching time vs. Collector current (typ.)

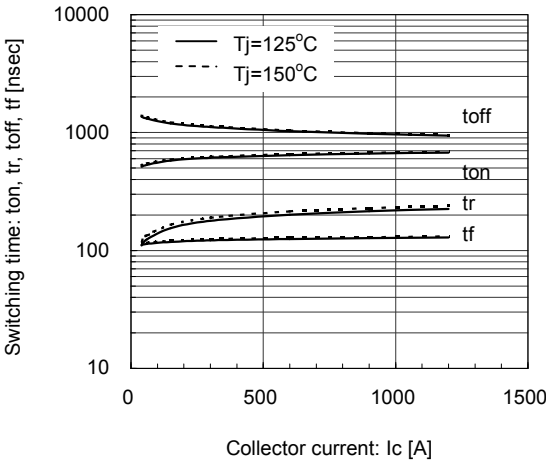
$V_{CC}=600V$, $V_{GE}=\pm 15V$, $R_g=0.62\Omega$, $T_j=25^\circ C$



[INVERTER]

Switching time vs. Collector current (typ.)

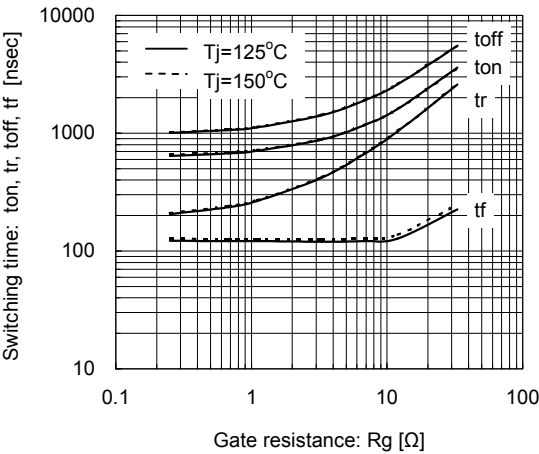
$V_{CC}=600V$, $V_{GE}=\pm 15V$, $R_g=0.62\Omega$, $T_j=125^\circ C, 150^\circ C$



[INVERTER]

Switching time vs. Gate resistance (typ.)

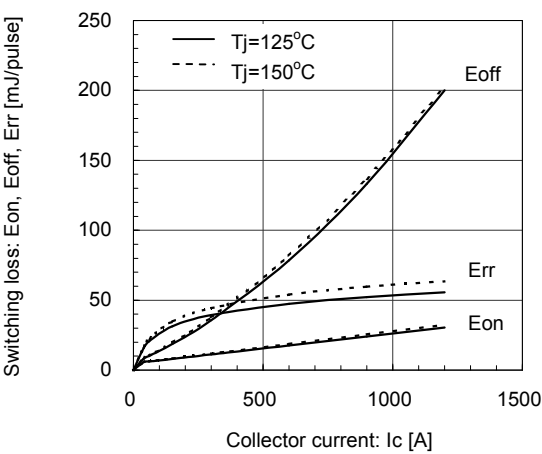
$V_{CC}=600V$, $I_c=600A$, $V_{GE}=\pm 15V$, $T_j=125^\circ C, 150^\circ C$



[INVERTER]

Switching loss vs. Collector current (typ.)

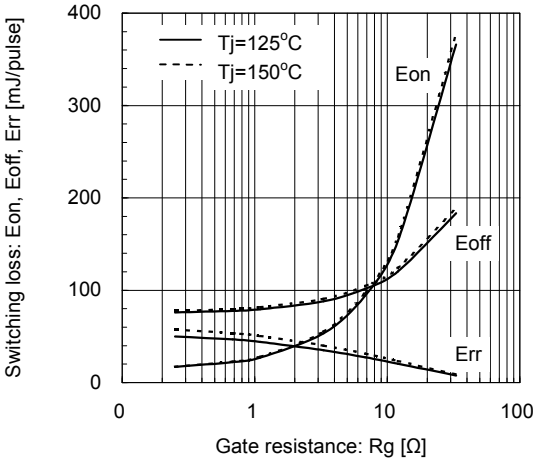
$V_{CC}=600V$, $V_{GE}=\pm 15V$, $R_g=0.62\Omega$, $T_j=125^\circ C, 150^\circ C$



[INVERTER]

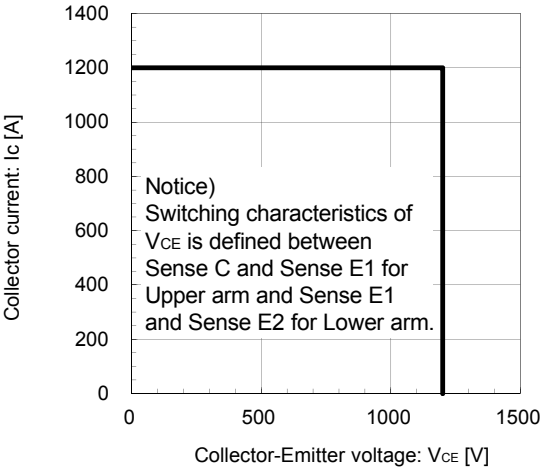
Switching loss vs. Gate resistance (typ.)

$V_{CC}=600V$, $I_c=600A$, $V_{GE}=\pm 15V$, $T_j=125^\circ C, 150^\circ C$

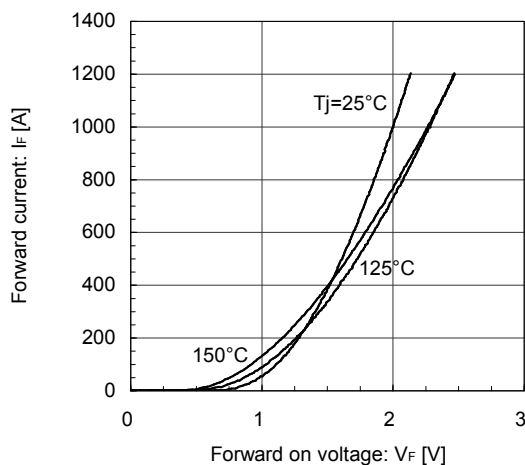


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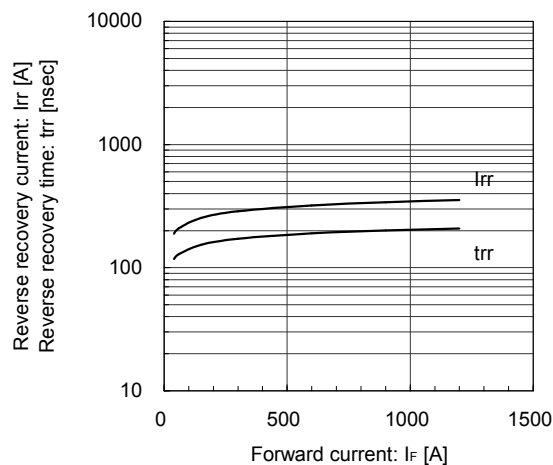
Reverse bias safe operating area (max.)
 $+V_{GE}=15V$, $-V_{GE}=15V$, $R_g=0.62\Omega$, $T_j=150^\circ C$



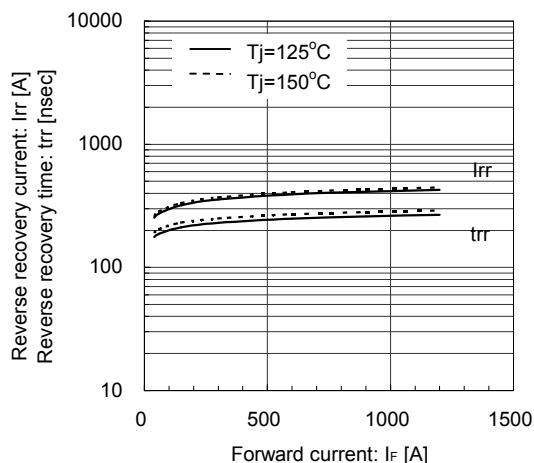
[INVERTER]

Forward Current vs. Forward Voltage (typ.)
chip

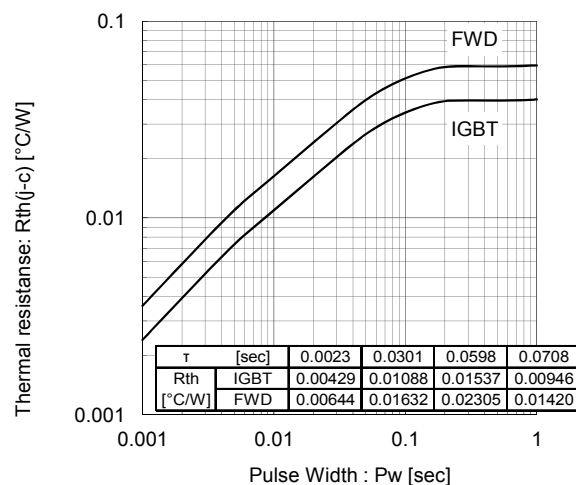
[INVERTER]

Reverse Recovery Characteristics (typ.)
 $V_{CC}=600V$, $V_{GE}=\pm 15V$, $R_g=0.62\Omega$, $T_J=25^\circ C$ 

[INVERTER]

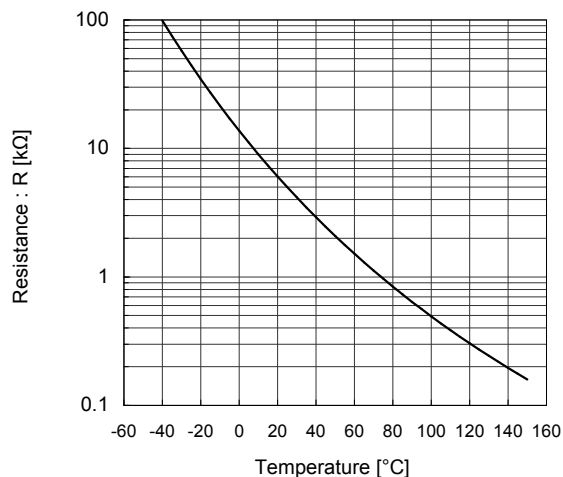
Reverse Recovery Characteristics (typ.)
 $V_{CC}=600V$, $V_{GE}=\pm 15V$, $R_g=0.62\Omega$, $T_J=125^\circ C$, $150^\circ C$ 

Transient Thermal Resistance (max.)

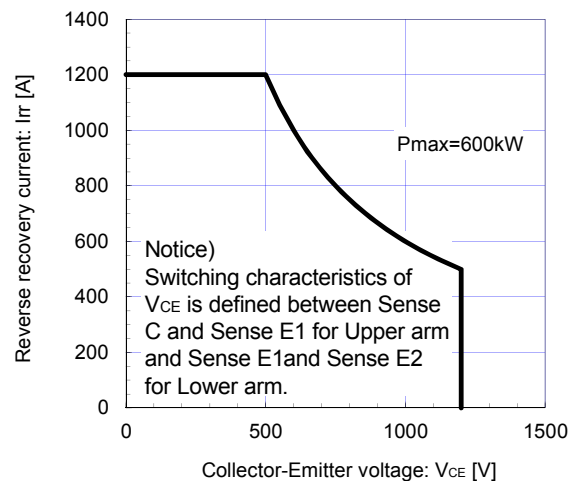


[THERMISTOR]

Temperature characteristic (typ.)



FWD safe operating area (max.)

 $T_J=150^\circ C$ 

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